

Amendments to the Claims

This listing of the claims will replace all prior versions and listings of claims in the application.

Listing of Claims:

1. (currently amended): A semiconductor connection comprising:
 - at least two active areas;
 - an electrically conductive doped channel providing an electrical connection between said at least two active areas; ~~and~~
 - a first conductive layer disposed over a first portion of said electrically conductive channel; and
 - a second conductive layer disposed over a second portion of said electrically conductive channel wherein said first and second conductive layers are spaced apart from one another and a third portion of the electrically conductive doped channel between said first conductive layer and said second conductive layer is uncovered.
2. (original): The semiconductor connection of claim 1 wherein said first and second conductive layers are silicide layers.
3. (original): The semiconductor connection of claim 1 wherein said electrically conductive doped channel comprises:
 - a first doped channel area adjacent to a first one of said at least two active areas;
 - a second doped channel area adjacent to a second one of said at least two active areas; and
 - a channel block structure disposed in between said first doped channel area and said second doped channel area.
4. (original): The semiconductor connection of claim 3 wherein said first doped channel area, said second doped channel area, and said channel block structure have a same conductivity type.

5. (original): The semiconductor connection of claim 3 wherein said at least two active areas have a first doping concentration and said channel block structure has a second doping concentration, said second doping concentration being less than said first doping concentration.

Claims 6-11 (canceled)